

**Scanning Tunneling Microscopy and Spectroscopy of Wet-Chemically  
Prepared Chlorinated Si(111) Surfaces**

**Supporting Information**

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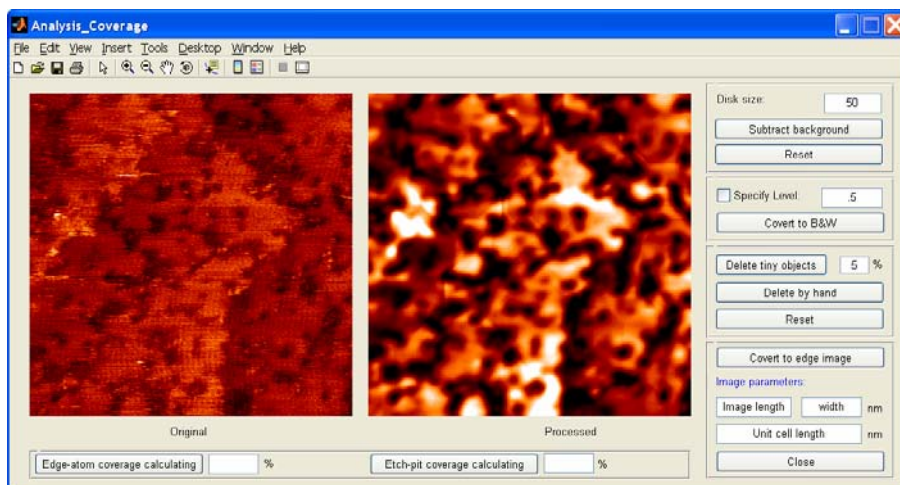
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## Supporting Information

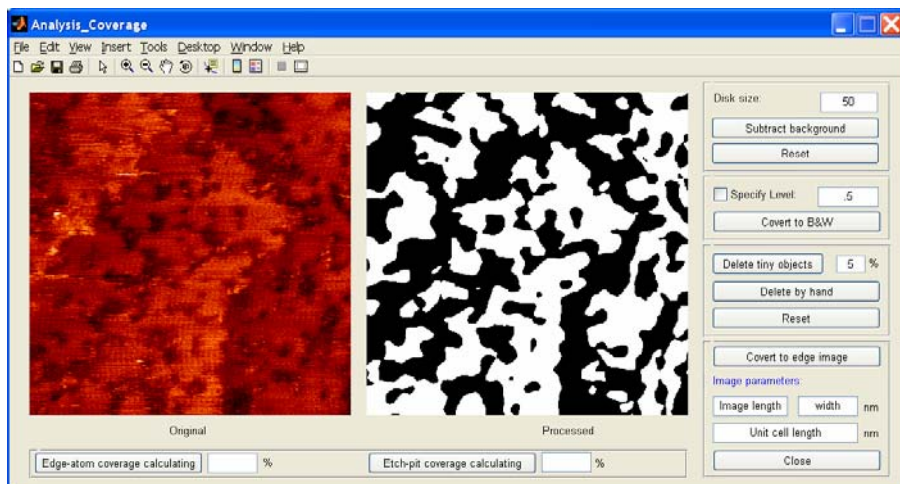
Etch-pit and edge-atom coverage calculation steps: (An approximate method)

1. Average and background subtraction;

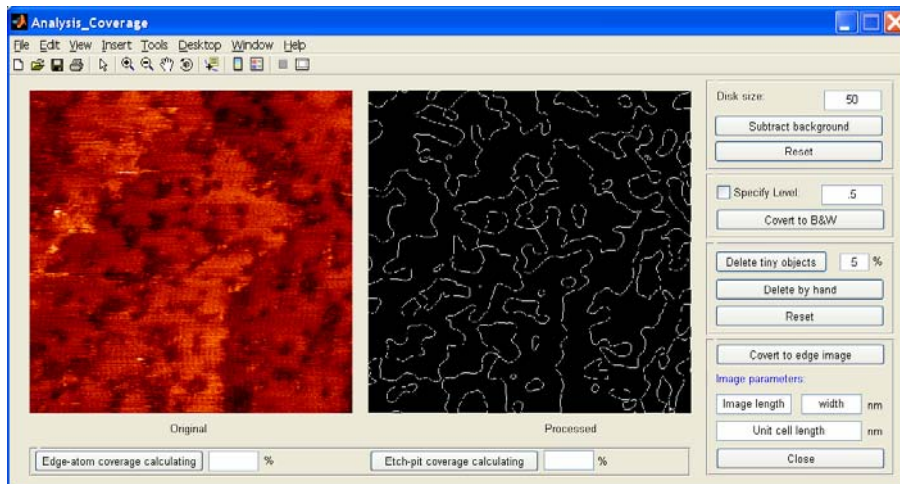


Note: different average level would lead to an error in the final result.

2. Converting to B&W images;



3. Converting to edge images;



4. Calculating the results;

